

CIR-V3DEHK1604G

DDR3 ECC-DIMM 1600MHz 4GB

Description

The CIR-V3DEHK1604G is 512M words X 72 bits, 1 rank. Unbuffered Dual In-Line Memory Module (ECC-DIMM). DDR3 SDRAMs in Fine Ball Grid Array (FBGA) packages on a 240pin glass-epoxy substrate. Provide a high performance 8 byte interface in 133.35mm width form factor of industry standard. It is suitable for easy interchange and addition.

Specifications

Density	4GB
Pin Count	240pin
Type	Unbuffered
Dimensions	133.35mm x 30.0mm
ECC	With ECC
Component Config	512M x 8 bit
Data Rate	1600 Mbps
CAS Latency	11
Voltage:	1.5V / 1.35V
PCB Layers	6
Operating Temp.(TCASE)	0°C~+85°C
Module Ranks	Single Rank

Features

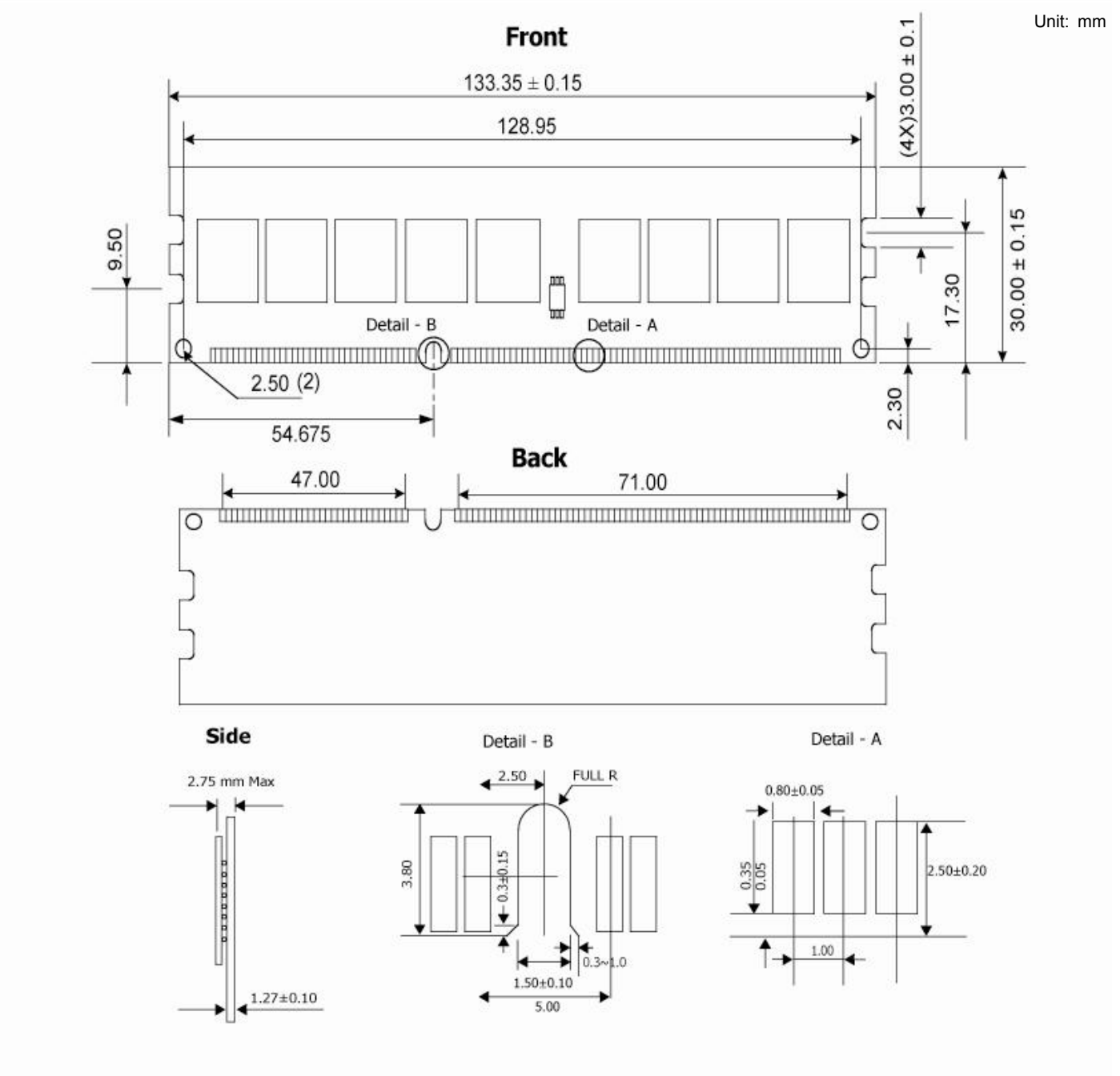
- Mounting 9 pieces of 4G bits DDR3 SDRAM sealed In FBGA
- Package: 240-pin socket type Unbuffered dual in line memory module (ECC-DIMM)
- Power Supply: VDD= 1.5V (1.425V to 1.575V) & VDD= 1.35V (1.283V to 1.45V)
- VDDSPD=3.0V to 3.6V
- Interface: SSTL_15
- CAS (READ) latency (CL): 6, 7, 8, 9, 10, 11
- Bi-Directional Differential Data Strobe
- Eight Internal banks for concurrent operation (components)
- Refresh: Auto-refresh, self-refresh
- Burst Length (BL) switch on-the-fly BL8 or BC4(Burst Chop)
- Supports ECC error correction and detection
- On-Die-Termination (ODT) for better signal quality
- Serial Presence-Detect (SPD) EEPROM with temperature sensor
- RoHS Compliant (Lead Free) Memory module
- TCASE of 0°C to 95°C (Components)
 - 64ms, 8,192 cycle refresh at 0°C to 85°C
 - 32ms at 85°C to 95°C



Speed Grade

Frequency Grade	Data Transfer Rate	CAS Latency Support						CL-tRCD-tRP
		CL6	CL7	CL8	CL9	CL10	CL11	
DDR3-1600	PC3-12800	800	1066	1066	1333	1333	1600	11-11-11

Package Dimensions



Tolerances : ± 0.15 mm unless otherwise specified